

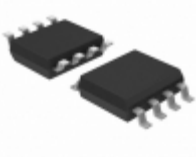




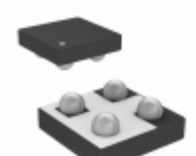

	<h2>SI8402DB-T1-E1</h2>
	<p><b>Hersteller-Teilenummer:</b> SI8402DB-T1-E1</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 20V 5.3A 2X2 4-MFP</p> <p><b>Datenblätter:</b>  <a href="#">SI8402DB-T1-E1.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 83858 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SI8402DB-T1-E1
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 20V 5.3A 2X2 4-MFP
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	83858 pcs Stock
detaillierte Beschreibung	N-Channel 20V 5.3A (Ta) 1.47W (Ta) Surface Mount 4-
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	4-XFBGA, CSPBGA
Supplier Device-Gehäuse	4-Microfoot
Verlustleistung (max)	1.47W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.3A (Ta)
Rds On (Max) @ Id, Vgs	37 mOhm @ 1A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	26nC @ 4.5V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI8402DB-T1-E1CT

SI8402DB-T1-E1 ist neu im Original, Suche SI8402DB-T1-E1 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI8402DB-T1-E1 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI8402DB-T1-E1: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI8402</b> SILICON SILICON WB SOIC</p>	 <p><b>SI8402AB-B-ISR</b> Energy Micro (Silicon Labs) DGTL ISO 2.5KV 2CH I2C 8SOIC</p>	 <p><b>SI8405AA-A-IS1</b> Energy Micro (Silicon Labs) DGTL ISOLATOR 1KV 4CH I2C 16SOIC</p>	 <p><b>SI8402AB-B-IS</b> Energy Micro (Silicon Labs) DGTL ISO 2.5KV 2CH I2C 8SOIC</p>
 <p><b>SI8402DB-T1-E1.</b> VIS SI8402DB-T1-E1. VIS</p>	 <p><b>SI8402DB-T1</b> VISHAY SI8402DB-T1 VISHAY</p>	 <p><b>SI8402DB-T1-E1</b> Vishay / Siliconix MOSFET N-CH 20V 5.3A 2X2 4- MFP</p>	 <p><b>SI8402DB-T1-E3</b> VISHAY SI8402DB-T1-E3 VISHAY</p>

heiße Teile

Mehr

SI8235BB-C-IS	SI8235BD-D-ISR	SI8236BB-C-IM	SI8238AD-D-ISR	SI8252-IMR
SI8261AAC-C-IS	SI8261ABD-C-IS	SI8261ACC-C-IS	SI8261BAC-C-IPR	SI8261BAC-C-IS
SI8261BAD-C-IS	SI8261BBC-C-IS	SI8261BBD-C-IS	SI8261BCC-C-IP	SI8261BCC-C-IS
SI8261BCD-C-IS	SI8388P-IU	SI8400AA-B-IS	SI8400AB-B-ISR	SI8401DB-T1
SI8401DB-T1-E1	SI8401DB-T1-E1	SI8401DB-T1-E3	SI8401DB-T1-E3	SI8402DB-T1
SI8402DB-T1-E1	SI8402DB-T1-E1.	SI8402DB-T1-E3	SI8404DB-T1-E1	SI8404DB-T1-E1
SI8405DB	SI8405DB-T1	SI8405DB-T1-E1	SI8405DB-T1-E1	SI8405DB-T1-E3
SI8405DB-T1-E3	SI8409DB-T1	SI8409DB-T1-E1	SI8409DB-T1-E1	SI8410AB
SI8410BB-D-ISR	SI8410BB-I-DS	SI8413DB-T1-E1	SI8413DB-T1-E1	SI8415DB-T1
SI8415DB-T1-E1	SI8415DB-T1-E1	SI8417DB-T2-E1	SI8417DB-T2-E1	SI8420BB

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